Diplete - CS (OLD SCHEME)

Code: DC02 Subject: FUNDAMENTALS OF ELECTRONICS
Time: 3 Hours Max. Marks: 100

JUNE 2011

NOTE: There are 9 Questions in all.

- Question 1 is compulsory and carries 20 marks. Answer to Q.1 must be written in the space provided for it in the answer book supplied and nowhere else.
- The answer sheet for the Q.1 will be collected by the invigilator after 45 Minutes of the commencement of the examination.
- Out of the remaining EIGHT Questions answer any FIVE Questions. Each question carries 16 marks.

Q.1	Choose the correct or the best alternative in the following:			
	a.	The input impedance of an	ideal op-amp is	
		(A) Zero.	(B) Infinity.	
		(C) 100Ω .	(D) Less than one.	
	b.	A resistor has a colour bar value is	nd sequence Green, Violet, Black and gold. Its	
		(A) $5.7 \Omega \pm 5\%$.	(B) 57 $\Omega \pm 5\%$.	
		(C) 570 $\Omega \pm 5\%$.	(D) 5.7 K $\Omega \pm 5\%$.	
	c.	Oscillators uses	feedback.	
		(A) Positive.	(B) Negative.	
		(C) Both (A) and (B).	(D) None of above.	
	d. An electron in the conduction band			
		• •	an electron in the valance band.	
		(C) has equal energy than an electron in the valance band.(D) has a higher energy than an electron in the valance band.		
	e. When the P-N junction is forward biased, width		is forward biased, width of depletion layer	is
		(A) reduced.	(B) increased.	
		(C) same as unbiased.	(D) none of above.	
	f.	The Schottky barrier diode	has	
		(A) one p-n junction.	(B) two p-n junction.	
DCOO	. ,	(C) no p-n junction.	(D) none of them is true. 1 DiplETE - CS (OLD SCHEME	- \

	g. In a junction transistor, which region is made narrower than the ot regions		ion is made narrower than the other two	
		(A) collector region.(C) emitter region.	(B) base region.(D) none of above.	
	h.	Which of the following is a univers	al gate	
		(A) AND (C) OR	(B) NAND (D) NOT	
	i.	The main advantage of CMOS is		
		(A) high speed.(C) low power consumption.	(B) low noise margins.(D) none of above.	
	j	The plastic DIP IC package is most	widely used, because	
		 (A) it has higher mechanical streng (B) it is only packing method availa (C) other type of packing method is (D) it is much cheaper than other ty 	able. s not reliable.	
		Answer any FIVE Questions of		
		Each question carri	es 16 marks.	
Q.2	a.		es 16 marks. Lytic capacitor with the help of its (8)	
Q.2		Explain the working of electron constructional details.	lytic capacitor with the help of its (8) rrent source into a voltage source. Also	
Q.2 Q.3	b.	Explain the working of electron constructional details. Explain how will you convert a custate and explain Thevenin's theore	lytic capacitor with the help of its (8) rrent source into a voltage source. Also m. (4+4) c semiconductors? Explain effect of	
	b.	Explain the working of electron constructional details. Explain how will you convert a custate and explain Thevenin's theore What are intrinsic and extrinsic temperature on conductivity of sem	rent source into a voltage source. Also m. (4+4) e semiconductors? Explain effect of iconductor. (4+4) y potential barrier is formed in a p-n	
	b. a. b.	Explain the working of electron constructional details. Explain how will you convert a custate and explain Thevenin's theore. What are intrinsic and extrinsic temperature on conductivity of sem. What is p-n junction diode? How junction diode? What is signification.	rent source into a voltage source. Also m. (4+4) e semiconductors? Explain effect of iconductor. (4+4) y potential barrier is formed in a p-n	

(4+4)

Q.5 a. Explain the transistor action with the help of suitable diagram and also

explain need for transistor biasing.

- b. Compare the CB, CE and CC configurations of a transistor. Draw input and output characteristics of a transistor in CB configuration. (4+4)
- Q.6 a. Explain the differences between positive and negative feedback amplifier. What are advantages & disadvantages of negative feedback amplifier? (4+4)
 - b. With the help of a diagram, explain the working of FET as a switch. Also list out the applications of FET. (4+4)
- **Q.7** a. Prove the following using Boolean algebra
 - (i) A (A+B) + A (B+C) + A (A+C) = A

(ii)
$$(A+B)(\overline{A}+C)(B+C) = AC+B\overline{A}$$
 (4+4)

b. Minimize the following logic functions using K- Map

$$f(A, B, C, D) = \sum m(1,3,5,8,9,11,15) + d(2,13)$$
 (8)

- Q.8 a. Draw schematic diagram of TTL NAND gate and explain its working. (8)
 - b. Draw symbol of EX-OR gate and explain its working using truth table.

 Also realize EX-OR gate using four NAND gates only. (4+4)
- **Q.9** a. What is IC? Explain how a capacitor can be constructed in a monolithic IC.(8)
 - b. Draw the schematic diagram of Integrator and Voltage Follower using op-amp and explain its working. (4+4)